Dual Bias Resistor Transistor

NPN and PNP Silicon Surface Mount Transistors with Monolithic Bias Resistor Network

- High Current: I_C = 500 mA max
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS $(T_A = 25^{\circ}C)$

Rating	Symbol	Value	Unit
Collector-Base Voltage	V _{(BR)CBO}	50	Vdc
Collector–Emitter Voltage	V _{(BR)CEO}	50	Vdc
Emitter-Base Voltage	V _{(BR)EBO}	5.0	Vdc
Collector Current – Continuous	Ic	500	mAdc

THERMAL CHARACTERISTICS

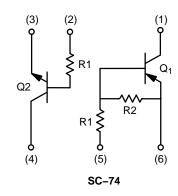
Characteristic	Symbol	Max	Unit	
Power Dissipation*	P_{D}	285	mW	
Junction Temperature	TJ	150	°C	
Storage Temperature	T _{stg}	-55 to +150	°C	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



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MARKING DIAGRAM



SC-74R 318AA Style 21



D10 = Specific Device Code

// = Date Code

= Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]
IMD10AMT1G	SC-74R (Pb-Free)	3000 / Tape & Reel
NSVIMD10AMT1G	SC-74R (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}Total for both Transistors.

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise noted, common for Q_1 and Q_2 , – minus sign for $Q_1(PNP)$ omitted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				•
Collector–Base Breakdown Voltage ($I_C = 50 \mu Adc, I_E = 0 A$)	V _(BR) CBO	50	-	Vdc
Collector–Emitter Breakdown Voltage (I _C = 1.0 mAdc, I _B = 0 A)	V _(BR) CEO	50	-	Vdc
Emitter–Base Breakdown Voltage ($I_E = 50 \mu Adc, I_C = 0 A$)	V _{(BR)EBO}	5.0	-	Vdc
Collector–Base Cutoff Current (V _{CB} = 50 Vdc, I _E = 0 A)	Ісво	-	100	nA
Emitter–Base Cutoff Current Q1 (PNP) $(V_{EB} = 6.0 \text{ Vdc}, I_{C} = 0 \text{ A})$ Q2 (NPN)	I _{EBO}	- -	1.0 0.5	mA
Collector–Emitter Cutoff Current (V _{CE} = 15 Vdc, I _B = 0 A)	I _{CEO}	_	500	nA
Collector–Emitter Cutoff Current (V _{CE} = 25 Vdc, I _B = 0 A)	I _{CES}	-	100	nA
ON CHARACTERISTICS (Note 1)				
DC Current Gain $(V_{CE} = 5.0 \text{ V}, I_{C} = 100 \text{ mA}) \text{ Q1(PNP)} $ $(V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA}) \text{ Q2(NPN)}$	h _{FE}	68 100	_ 600	
Collector–Emitter Saturation Voltage (I _C = 10 mA, I _B = 1.0 mA)	V _{CE(sat)}	-	0.3	Vdc
Output Voltage (on) $(V_{CC} = 5.0 \text{ V}, V_B = 2.5 \text{ V}, R_L = 1.0 \text{ k}\Omega)$	V _{OL}	-	0.2	Vdc
Output Voltage (off) (V _{CC} = 5.0 V, V _B = 0.25 V, R _L = 1.0 k Ω)	V _{ОН}	4.9	-	Vdc
Input Resistor Q1(PNP) Q2(NPN)	R1	70 7.0	130 13	Ω k Ω
Resistor Ratio Q1(PNP) Q2(NPN)	R1/R2	0.008	0.012	

^{1.} Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle < 2.0%.

TYPICAL CHARACTERISTICS (NPN)

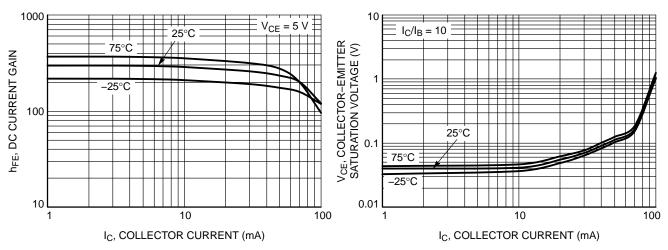


Figure 1. DC Current Gain

Figure 2. Collector-Emitter Saturation Voltage

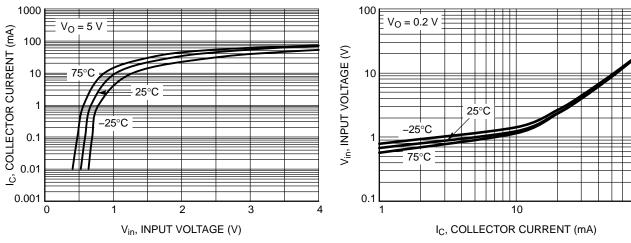


Figure 3. Output Current vs. Input Voltage

Figure 4. Input Voltage vs. Output Current

100

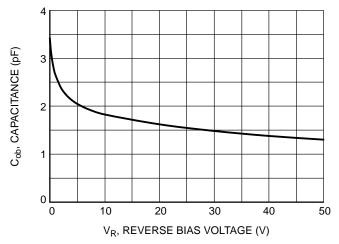


Figure 5. Output Capacitance

TYPICAL CHARACTERISTICS (PNP)

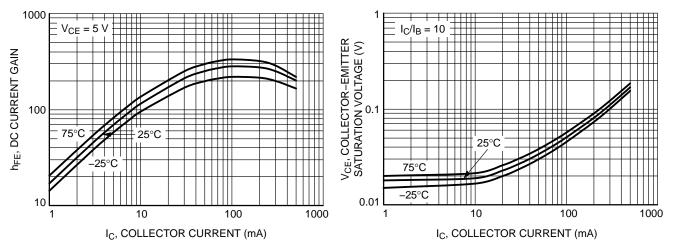


Figure 6. DC Current Gain

Figure 7. Collector-Emitter Saturation Voltage

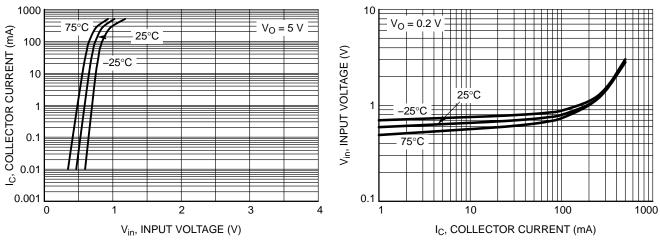


Figure 8. Output Current vs. Input Voltage

Figure 9. Input Voltage vs. Output Current

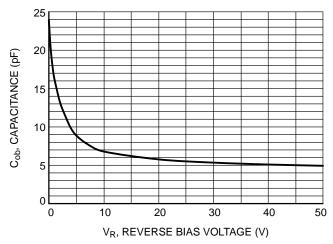
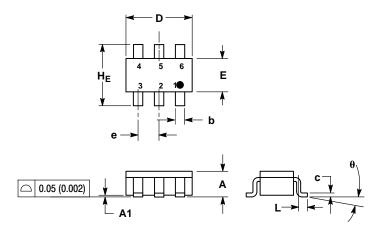


Figure 10. Output Capacitance

PACKAGE DIMENSIONS

SC-74R CASE 318AA ISSUE B



NOTES

- 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982
- CONTROLLING DIMENSION: INCH.
 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD
 THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL

	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.90	1.00	1.10	0.035	0.039	0.043	
A1	0.01	0.06	0.10	0.001	0.002	0.004	
b	0.25	0.37	0.50	0.010	0.015	0.020	
С	0.10	0.18	0.26	0.004	0.007	0.010	
D	2.90	3.00	3.10	0.114	0.118	0.122	
E	1.30	1.50	1.70	0.051	0.059	0.067	
е	0.85	0.95	1.05	0.034	0.037	0.041	
L	0.20	0.40	0.60	0.008	0.016	0.024	
HE	2.50	2.75	3.00	0.099	0.108	0.118	
θ		-			_		

10°

0°

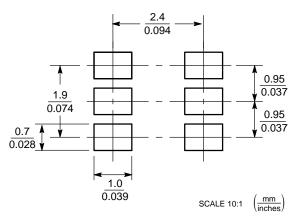
10°

STYLE 21:

- PIN 1. COLLECTOR 1 2. EMITTER 2

 - 3. BASE 2
 - **COLLECTOR 2** 5. EMITTER 1

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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